

TO-92 Plastic-Encapsulate Transistors

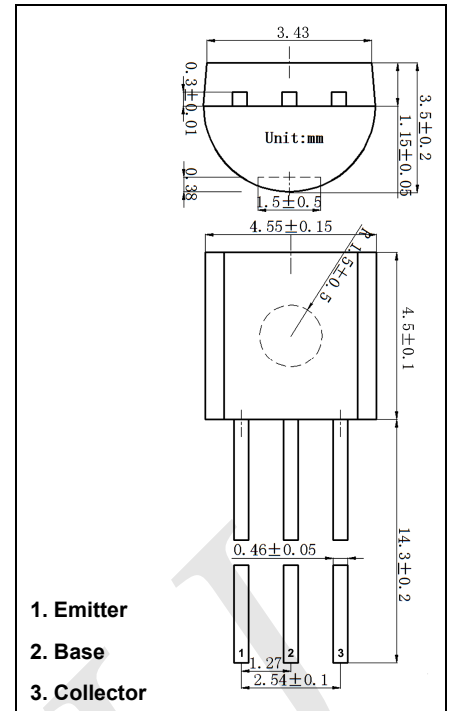
S9015C331 PNP Transistors

Features

- High Total Power Dissipation ($P_C = 0.45W$)
- High h_{FE} and Good Linearity
- Complementary to S9014

Maximum Ratings ($T_a=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-50	V
V_{CEO}	Collector Emitter Voltage	-45	V
V_{EBO}	Emitter Base Voltage	-5	V
I_C	Collector Current	-0.1	A
P_C	Collector Power Dissipation	450	mW
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55 ~ +150	$^\circ C$



Electrical Characteristics ($T_a=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	-50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -1mA, I_B = 0$	-45			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB} = -50V, I_E = 0$			-50	nA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V, I_C = 0$			-50	nA
$h_{FE(1)}$	DC current gain	$V_{CE} = -5V, I_C = -1mA$	200		300	
$h_{FE(2)}$		$V_{CE} = -5V, I_C = -10mA$	90			
$h_{FE(3)}$		$V_{CE} = -5V, I_C = -50mA$	50			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -100mA, I_B = -10mA$			-0.3	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = -100mA, I_B = -10mA$			-1.0	V
f_T	Transition frequency	$V_{CE} = -5V, I_C = -10mA, f = 30MHz$	100			MHz

Typical Characteristics

